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Irish Standard  
I.S. EN 60749-28:2017

# Semiconductor devices - Mechanical and climatic test methods - Part 28: Electrostatic discharge (ESD) sensitivity testing - Charged device model (CDM) - device level

**I.S. EN 60749-28:2017**

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## National Foreword

I.S. EN 60749-28:2017 is the adopted Irish version of the European Document EN 60749-28:2017, Semiconductor devices - Mechanical and climatic test methods - Part 28: Electrostatic discharge (ESD) sensitivity testing - Charged device model (CDM) - device level

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**EN 60749-28**

June 2017

ICS 31.080.01

English Version

**Semiconductor devices - Mechanical and climatic test methods -  
Part 28: Electrostatic discharge (ESD) sensitivity testing -  
Charged device model (CDM) - device level  
(IEC 60749-28:2017)**

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mécaniques et climatiques - Partie 28: Essai de sensibilité  
aux décharges électrostatiques (DES) - Modèle de dispositif  
chargé par contact direct (DC-CDM)  
(IEC 60749-28:2017)

Halbleiterbauelemente - Mechanische und klimatische  
Prüfverfahren - Teil 28: Prüfung der Empfindlichkeit gegen  
elektrostatische Entladungen (ESD) - Charged Device  
Model (CDM) - Device Level  
(IEC 60749-28:2017)

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## **EN 60749-28:2017**

### **European foreword**

The text of document 47/2362/FDIS, future edition 1 of IEC 60749-28, prepared by IEC/TC 47 "Semiconductor devices" in collaboration with IEC/TC 101 "Electrostatics" was submitted to the IEC-CENELEC parallel vote and approved by CENELEC as EN 60749-28:2017.

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IEC 60749-26	NOTE	Harmonized as EN 60749-26.
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# INTERNATIONAL STANDARD



**Semiconductor devices – Mechanical and climatic test methods –  
Part 28: Electrostatic discharge (ESD) sensitivity testing – Charged device  
model (CDM) – device level**



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**IEC 60749-28**

Edition 1.0 2017-03

# INTERNATIONAL STANDARD



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**Semiconductor devices – Mechanical and climatic test methods –  
Part 28: Electrostatic discharge (ESD) sensitivity testing – Charged device  
model (CDM) – device level**

INTERNATIONAL  
ELECTROTECHNICAL  
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## CONTENTS

FOREWORD.....	5
INTRODUCTION.....	7
1 Scope.....	8
2 Normative references .....	8
3 Terms and definitions .....	8
4 Required equipment .....	9
4.1 CDM ESD tester .....	9
4.1.1 General .....	9
4.1.2 Current-sensing element.....	10
4.1.3 Ground plane.....	10
4.1.4 Field plate/field plate dielectric layer.....	10
4.1.5 Charging resistor .....	11
4.2 Waveform measurement equipment .....	11
4.2.1 General .....	11
4.2.2 Cable assemblies .....	11
4.2.3 Equipment for high-bandwidth waveform measurement .....	11
4.2.4 Equipment for 1,0 GHz waveform measurement .....	11
4.3 Verification modules (metal discs).....	11
4.4 Capacitance meter.....	11
4.5 Ohmmeter.....	12
5 Periodic tester qualification, waveform records, and waveform verification requirements .....	12
5.1 Overview of required CDM tester evaluations.....	12
5.2 Waveform capture hardware .....	12
5.3 Waveform capture setup .....	12
5.4 Waveform capture procedure .....	12
5.5 CDM tester qualification/requalification procedure .....	13
5.5.1 CDM tester qualification/requalification procedure .....	13
5.5.2 Conditions requiring CDM tester qualification/requalification.....	13
5.5.3 1 GHz oscilloscope correlation with high bandwidth oscilloscope .....	14
5.6 CDM tester quarterly and routine waveform verification procedure .....	14
5.6.1 Quarterly waveform verification procedure .....	14
5.6.2 Routine waveform verification procedure .....	14
5.7 Waveform characteristics .....	14
5.8 Documentation.....	16
5.9 Procedure for evaluating full CDM tester charging of a device .....	16
6 CDM ESD testing requirements and procedures .....	17
6.1 Device handling .....	17
6.2 Test requirements .....	17
6.2.1 Test temperature and humidity .....	17
6.2.2 Device test .....	17
6.3 Test procedures.....	17
6.4 CDM test recording / reporting guidelines .....	18
7 CDM classification criteria .....	18
Annex A (normative) Verification module (metal disc) specifications and cleaning guidelines for verification modules and testers.....	19

A.1	Tester verification modules and field plate dielectric .....	19
A.2	Care of verification modules.....	19
Annex B (normative) Capacitance measurement of verification modules (metal discs) sitting on a tester field plate dielectric .....		20
Annex C (informative) CDM test hardware and metrology improvements.....		21
Annex D (informative) CDM tester electrical schematic .....		23
Annex E (informative) Sample oscilloscope setup and waveform .....		24
E.1	General.....	24
E.2	Settings for the 1 GHz bandwidth oscilloscope .....	24
E.3	Settings for the high-bandwidth oscilloscope .....	24
E.4	Setup .....	24
E.5	Sample waveforms from a 1 GHz oscilloscope .....	24
E.6	Sample waveforms from an 8 GHz oscilloscope .....	25
Annex F (informative) Field-induced CDM tester discharge procedures.....		27
F.1	General.....	27
F.2	Single discharge procedure.....	27
F.3	Dual discharge procedure .....	27
Annex G (informative) Waveform verification procedures .....		29
G.1	Factor/offset adjustment method .....	29
G.2	Software voltage adjustment method.....	32
G.3	Example parameter recording tables .....	34
Annex H (informative) Determining the appropriate charge delay for full charging of a large module or device.....		36
H.1	General.....	36
H.2	Procedure for charge delay determination .....	36
Annex I (informative) Electrostatic discharge (ESD) sensitivity testing direct contact charged device model (DC-CDM).....		38
I.1	General.....	38
I.2	Standard test module .....	38
I.3	Test equipment (CDM simulator).....	38
I.3.1	Test equipment design.....	38
I.3.2	DUT (device under test) support .....	38
I.3.3	Metal bar/board .....	39
I.3.4	Equipment setup.....	39
I.4	Verification of test equipment.....	39
I.4.1	General description of verification test equipment.....	39
I.4.2	Instruments for measurement .....	41
I.4.3	Verification of test equipment, using a current probe .....	41
I.5	Test procedure.....	42
I.5.1	Initial measurement .....	42
I.5.2	Tests .....	42
I.5.3	Intermediate and final measurement .....	43
I.6	Failure criteria.....	43
I.7	Classification criteria.....	43
I.8	Summary .....	43
Bibliography.....		44
Figure 1 – Simplified CDM tester hardware schematic .....		10

Figure 2 – CDM characteristic waveform and parameters .....	16
Figure D.1 – Simplified CDM tester electrical schematic .....	23
Figure E.1 – 1 GHz TC 500, small verification module .....	25
Figure E.2 – 1 GHz TC 500, large verification module .....	25
Figure E.3 – 8 GHz TC 500, small verification module (oscilloscope adjusts for attenuation) .....	26
Figure E.4 – GHz TC 500, large verification module (oscilloscope adjusts for attenuation) .....	26
Figure F.1 – Single discharge procedure (field charging, $I_{\text{CDM}}$ Pulse, and slow discharge) .....	27
Figure F.2 – Dual discharge procedure (field charging, 1st $I_{\text{CDM}}$ pulse, no field, 2nd $I_{\text{CDM}}$ pulse) .....	28
Figure G.1 – An example of a waveform verification flow for qualification and quarterly checks using the factor/offset adjustment method .....	30
Figure G.2 – An example of a waveform verification flow for the routine checks using the factor/offset adjustment method .....	31
Figure G.3 – Example of average $I_{\text{peak}}$ for the large verification module – high bandwidth oscilloscope .....	32
Figure G.4 – An example of a waveform verification flow for qualification and quarterly checks using the software voltage adjustment method .....	33
Figure G.5 – An example of a waveform verification flow for the routine checks using the software voltage adjustment method .....	34
Figure H.1 – An example characterization of charge delay vs. $I_{\text{p}}$ .....	37
Figure I.1 – Examples of discharge circuit where the discharge is caused by closing the switch .....	39
Figure I.2 – Verification test equipment for measuring the discharge current flowing to the metal bar/board from the standard test module .....	40
Figure I.3 – Current waveform .....	40
Figure I.4 – Measurement circuit for verification method using a current probe .....	41
Table 1 – CDM waveform characteristics for a 1 GHz bandwidth oscilloscope .....	15
Table 2 – CDM waveform characteristics for a high-bandwidth ( $\geq 6$ GHz) oscilloscope .....	15
Table 3 – CDM ESDS device classification levels .....	18
Table A.1 – Specification for CDM tester verification modules (metal discs) .....	19
Table G.1 – Example waveform parameter recording table for the factor/offset adjustment method .....	35
Table G.2 – Example waveform parameter recording table for the software voltage adjustment method .....	35
Table I.1 – Dimensions of the standard test modules .....	38
Table I.2 – Specified current waveform .....	40
Table I.3 – Range of peak current $I_{\text{p1}}$ for test equipment .....	41
Table I.4 – Specification of peak current $I_{\text{p1}}$ for the current probe verification method .....	42

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### **SEMICONDUCTOR DEVICES – MECHANICAL AND CLIMATIC TEST METHODS –**

#### **Part 28: Electrostatic discharge (ESD) sensitivity testing – Charged device model (CDM) – device level**

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This standard is based on ESDA/JEDEC Joint Standard ANSI/ESDA/JEDEC JS-002 which resulted from the merging of JESD22-C101 and ANSI/ESD S5.3.1). It contains the essential elements from both standards. The co-operation of ANSI/ESDA/JEDEC is gratefully acknowledged.

The text of this International Standard is based on the following documents:

FDIS	Report on voting
47/2362/FDIS	47/2379/RVD

Full information on the voting for the approval of this International Standard can be found in the report on voting indicated in the above table.

This document has been drafted in accordance with the ISO/IEC Directives, Part 2.

A list of all parts in the IEC 60749 series, published under the general title *Semiconductor devices –Mechanical and climatic test methods*, can be found on the IEC website.

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## INTRODUCTION

The earliest electrostatic discharge (ESD) test models and standards simulate a charged object approaching a device and discharging through the device. The most common example is IEC 60749-26, the human body model (HBM). However, with the increasing use of automated device handling systems, another potentially destructive discharge mechanism, the charged device model (CDM), becomes increasingly important. In the CDM, a device itself becomes charged (e.g. by sliding on a surface (tribocharging) or by electric field induction) and is rapidly discharged (by an ESD event) as it closely approaches a conductive object. A critical feature of the CDM is the metal-metal discharge, which results in a very rapid transfer of charge through an air breakdown arc. The CDM test method also simulates metal-metal discharges arising from other similar scenarios, such as the discharging of charged metal objects to devices at different potential.

Accurately quantifying and reproducing this fast metal-metal discharge event is very difficult, if not impossible, due to the limitations of the measuring equipment and its influence on the discharge event. The CDM discharge is generally completed in a few nanoseconds, and peak currents of tens of amperes have been observed. The peak current into the device will vary considerably depending on a large number of factors, including package type and parasitics. The typical failure mechanism observed in MOS devices for the CDM model is dielectric damage, although other damage has been noted.

The CDM charge voltage sensitivity of a given device is package dependent. For example, the same integrated circuit (IC) in a small area package can be less susceptible to CDM damage at a given voltage compared to that same IC in a package of the same type with a larger area. It has been shown that CDM damage susceptibility correlates better to peak current levels than charge voltage.

## **SEMICONDUCTOR DEVICES – MECHANICAL AND CLIMATIC TEST METHODS –**

### **Part 28: Electrostatic discharge (ESD) sensitivity testing – Charged device model (CDM) – device level**

#### **1 Scope**

This part of IEC 60749 establishes the procedure for testing, evaluating, and classifying devices and microcircuits according to their susceptibility (sensitivity) to damage or degradation by exposure to a defined field-induced charged device model (CDM) electrostatic discharge (ESD). All packaged semiconductor devices, thin film circuits, surface acoustic wave (SAW) devices, opto-electronic devices, hybrid integrated circuits (HICs), and multi-chip modules (MCMs) containing any of these devices are to be evaluated according to this document. To perform the tests, the devices are assembled into a package similar to that expected in the final application. This CDM document does not apply to socketed discharge model testers. This document describes the field-induced (FI) method. An alternative, the direct contact (DC) method, is described in Annex I.

The purpose of this document is to establish a test method that will replicate CDM failures and provide reliable, repeatable CDM ESD test results from tester to tester, regardless of device type. Repeatable data will allow accurate classifications and comparisons of CDM ESD sensitivity levels.

#### **2 Normative references**

There are no normative references in this document.

#### **3 Terms and definitions**

For the purposes of this document, the following terms and definitions apply.

ISO and IEC maintain terminological databases for use in standardization at the following addresses:

- IEC Electropedia: available at <http://www.electropedia.org/>
- ISO Online browsing platform: available at <http://www.iso.org/obp>

##### **3.1**

##### **CDM ESD**

charged device model electrostatic discharge

electrostatic discharge (ESD) using the charged device model (CDM) to simulate the actual discharge event that occurs when a charged device is quickly discharged to another object at a lower electrostatic potential through a single pin or terminal

##### **3.2**

##### **CDM ESD tester**

charged device model electrostatic discharge tester

equipment that simulates the device level CDM ESD event using the non-socketed test method

Note 1 to entry: "Equipment" is referred to as "tester" in this document.



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